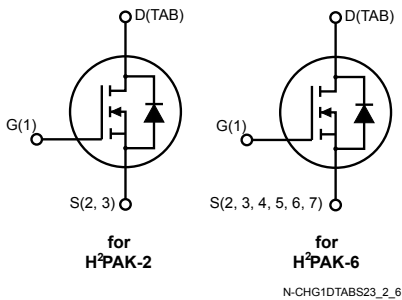
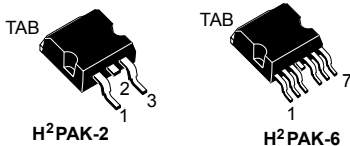


N-channel 100 V, 2 mΩ typ., 180 A STripFET™ F7 Power MOSFETs in an H²PAK-2 and H²PAK-6 packages



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STH240N10F7-2	100 V	2.5 mΩ	180 A
STH240N10F7-6			

- Among the lowest R_{DS(on)} on the market
- Excellent FoM (figure of merit)
- Low C_{rss}/C_{iss} ratio for EMI immunity
- High avalanche ruggedness

Description

These N-channel Power MOSFETs utilize STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Product status	
STH240N10F7-2	
STH240N10F7-6	
Product summary	
Order code	STH240N10F7-2
Marking	240N10F7
Package	H ² PAK-2
Packing	Tape and reel
Order code	STH240N10F7-6
Marking	240N10F7
Package	H ² PAK-6
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	180	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	120	A
$I_{DM}^{(2)}$	Drain current (pulsed)	720	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	300	W
$E_{AS}^{(3)}$	Single pulse avalanche energy	500	mJ
T_j	Operating junction temperature range	-55 to 175	$^\circ\text{C}$
T_{stg}	Storage temperature range		

1. Current limited by package.
2. Pulse width limited by safe operating area.
3. Starting $T_j=25\text{ }^\circ\text{C}$, $I_D=45\text{ A}$, $V_{DD}=50\text{ V}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.5	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	35	$^\circ\text{C/W}$

1. When mounted on 1 inch² FR-4, 2 Oz copper board.

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 3. On/Off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0\ \text{V}$	100			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\ \text{V}$, $V_{DS} = 100\ \text{V}$			1	μA
		$V_{GS} = 0\ \text{V}$, $V_{DS} = 100\ \text{V}$, $T_C = 125\text{ °C}$ ⁽¹⁾			100	μA
I_{GSS}	Gate-body leakage current	$V_{GS} = \pm 20\ \text{V}$, $V_{DS} = 0\ \text{V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	2.5		4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\ \text{V}$, $I_D = 60\ \text{A}$		2	2.5	m Ω

1. Defined by design, not subject to production test.

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\ \text{V}$, $f = 1\ \text{MHz}$, $V_{GS} = 0\ \text{V}$	-	11550	-	pF
C_{oss}	Output capacitance		-	2950	-	pF
C_{riss}	Reverse transfer capacitance		-	217	-	pF
Q_g	Total gate charge	$V_{DD} = 50\ \text{V}$, $I_D = 180\ \text{A}$,	-	160	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 0$ to $10\ \text{V}$	-	48	-	nC
Q_{gd}	Gate-drain charge	(see Figure 15. Test circuit for gate charge behavior)	-	38	-	nC

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 50\ \text{V}$, $I_D = 90\ \text{A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\ \text{V}$ (see Figure 14. Test circuit for resistive load switching times and Figure 19. Switching time waveform)	-	49	-	ns
t_r	Rise time		-	139	-	ns
$t_{d(off)}$	Turn-off delay time		-	110	-	ns
t_f	Fall time		-	112	-	ns

Table 6. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		180	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		720	A

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(2)}$	Source-drain curren	$I_{SD} = 180 \text{ A}$, $V_{GS} = 0 \text{ V}$	-		1.2	V
t_{rr}	Reverse recovery time	$I_{SD} = 180 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$	-	108		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 64 \text{ V}$, $T_J = 150 \text{ }^\circ\text{C}$ (see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	315		nC
I_{RRM}	Reverse recovery current		-	5.8		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%.

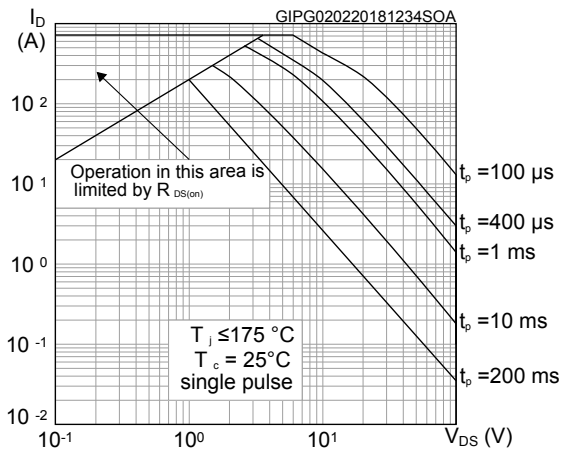
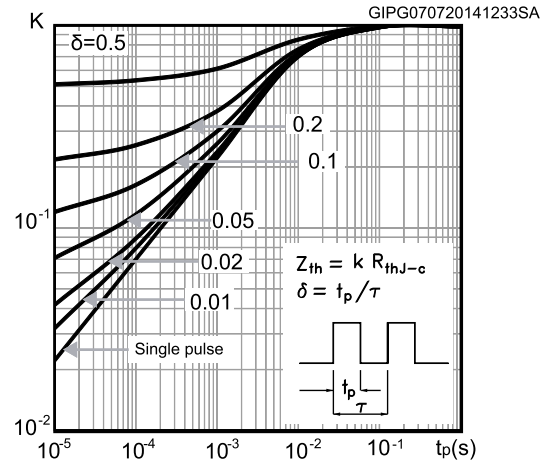
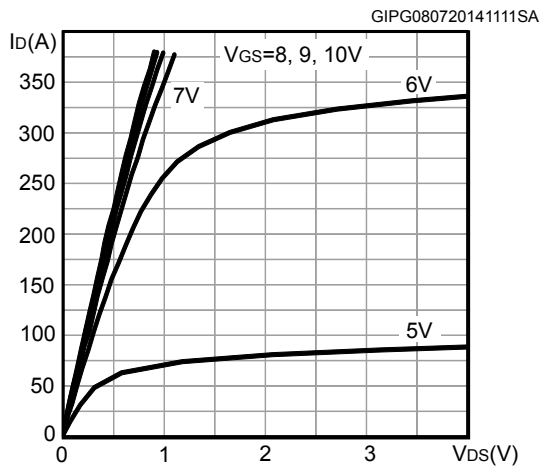
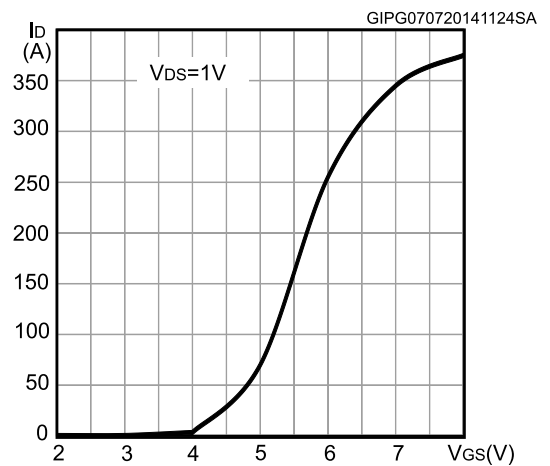
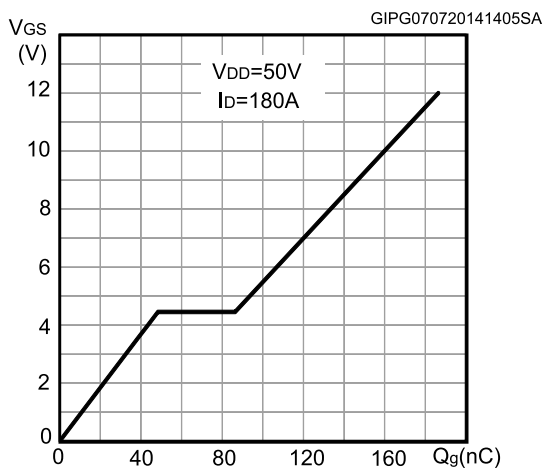
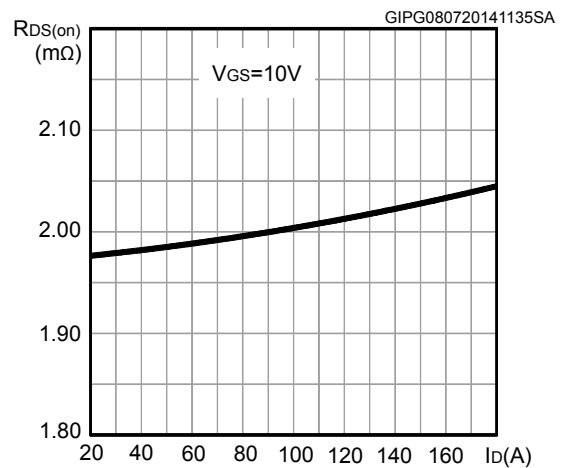
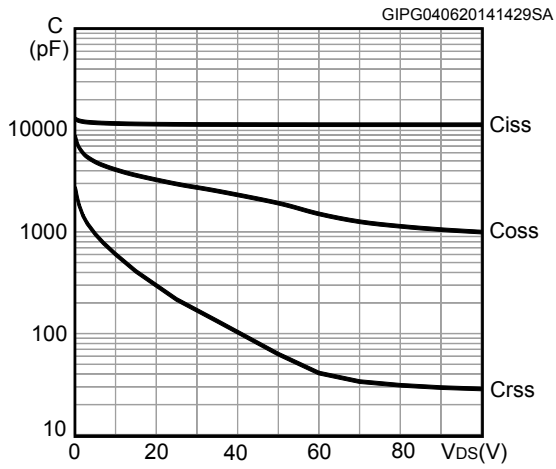
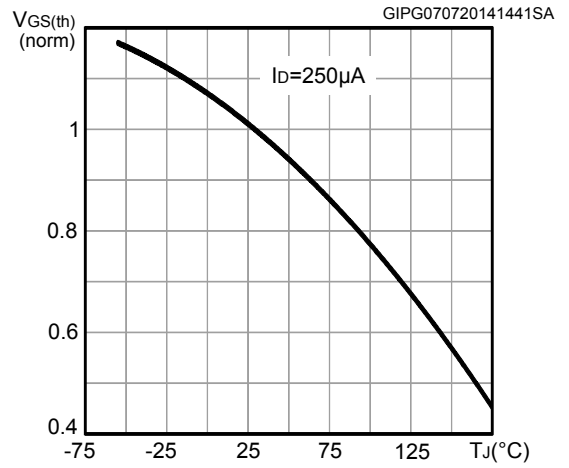
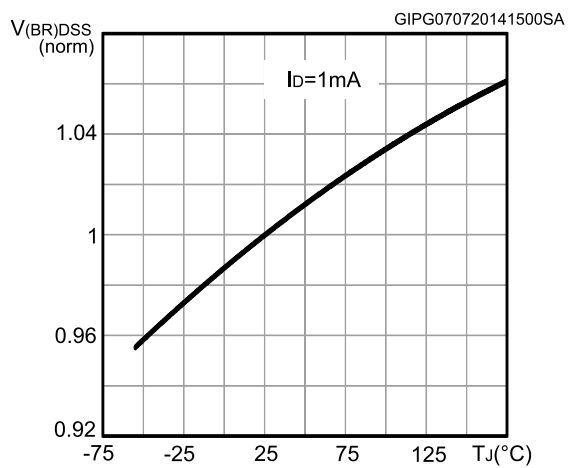
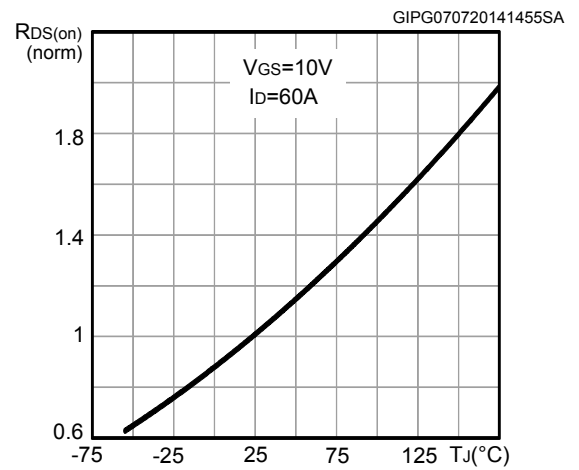
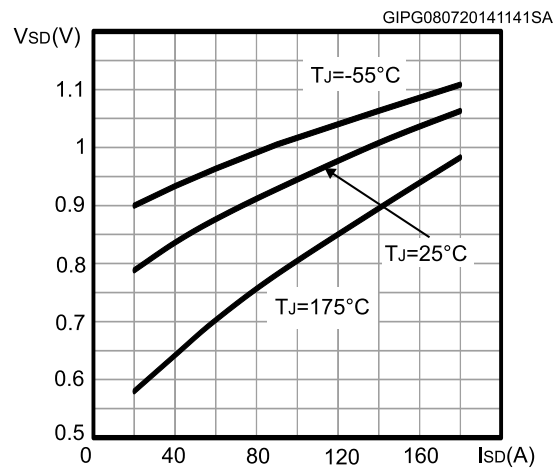
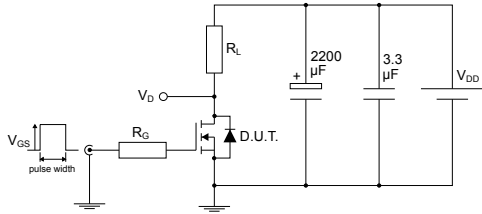
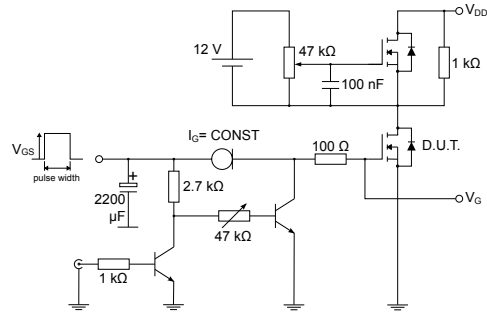
2.1 Electrical characteristics (curves)
Figure 3. Safe operating area

Figure 4. Thermal impedance

Figure 5. Output characteristics

Figure 6. Transfer characteristics

Figure 7. Gate charge vs gate-source voltage

Figure 8. Static drain-source on-resistance


Figure 9. Capacitance variations

Figure 10. Normalized gate threshold voltage vs. temperature

Figure 11. Normalized V_{(BR)DSS} vs. temperature

Figure 12. Normalized on-resistance vs. temperature

Figure 13. Source-drain diode forward characteristics


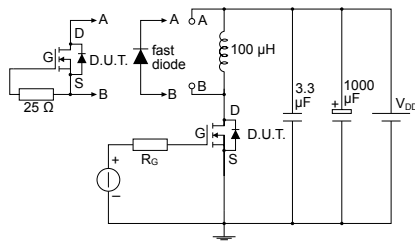
3 Test circuits

Figure 14. Test circuit for resistive load switching times


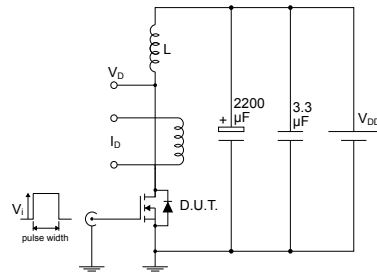
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Figure 15. Test circuit for gate charge behavior


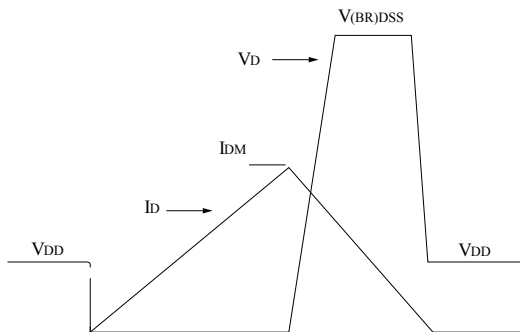
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Figure 16. Test circuit for inductive load switching and diode recovery times


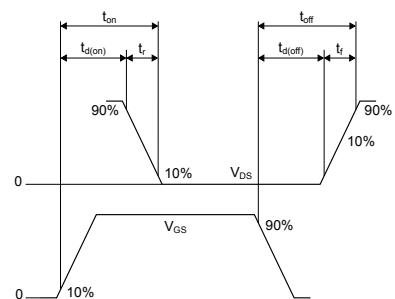
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Figure 17. Unclamped inductive load test circuit


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Figure 18. Unclamped inductive waveform


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Figure 19. Switching time waveform


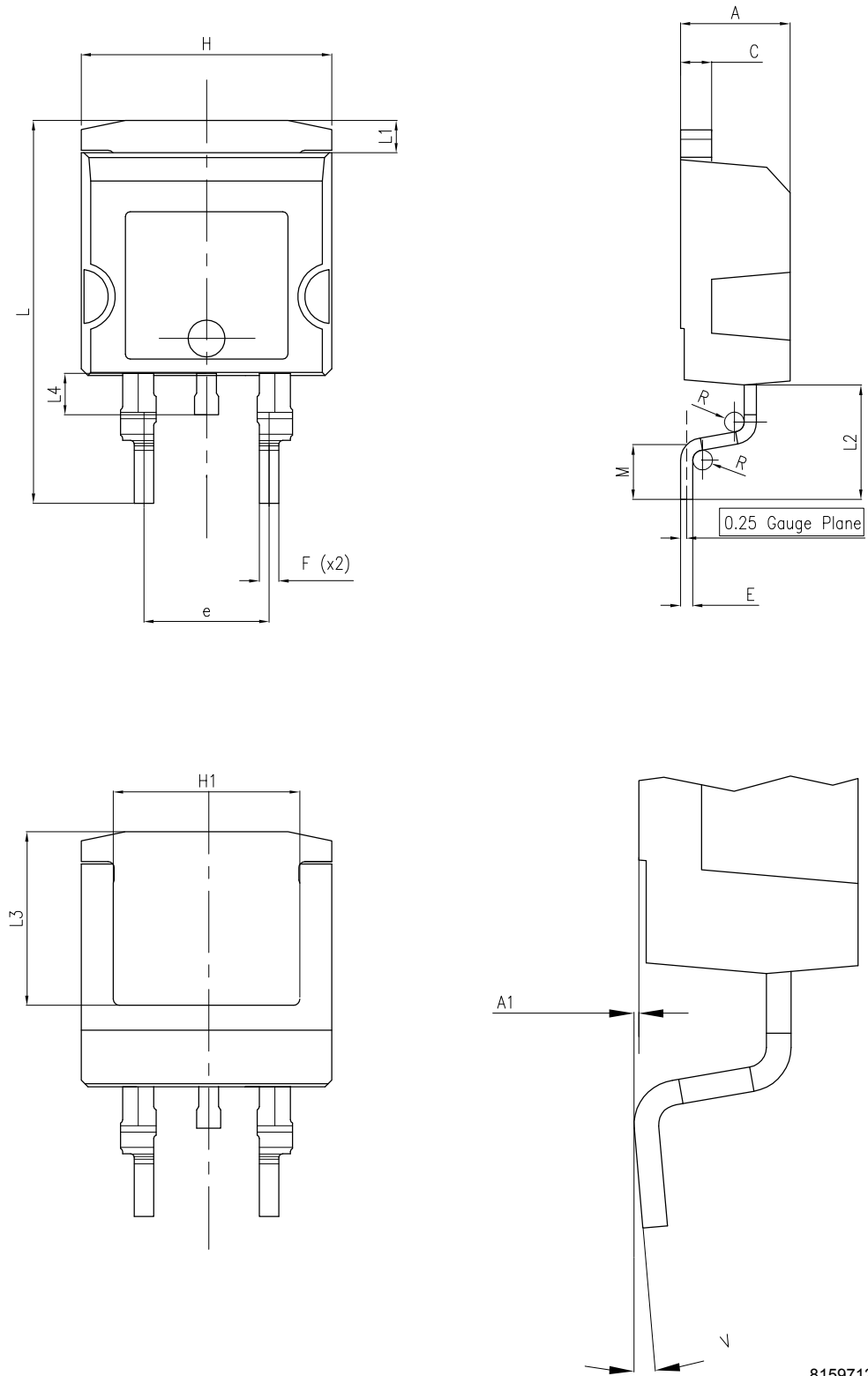
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 H²PAK-2 package information

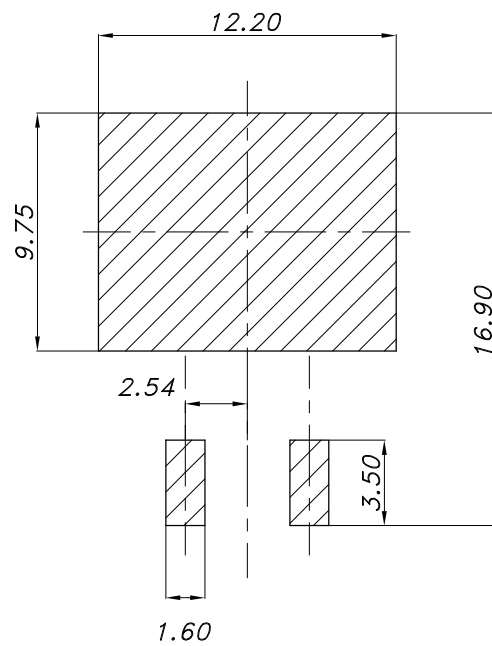
Figure 20. H²PAK-2 package outline



8159712_6

Table 7. H²PAK-2 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30		4.70
A1	0.03		0.20
C	1.17		1.37
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
H	10.00		10.40
H1	7.40		7.80
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.5		1.7
M	2.6		2.9
R	0.20		0.60
V	0°		8°

Figure 21. H²PAK-2 recommended footprint


8159712_6

Note: Dimensions are in mm.

4.2 H²PAK-6 package information

Figure 22. H²PAK-6 package outline

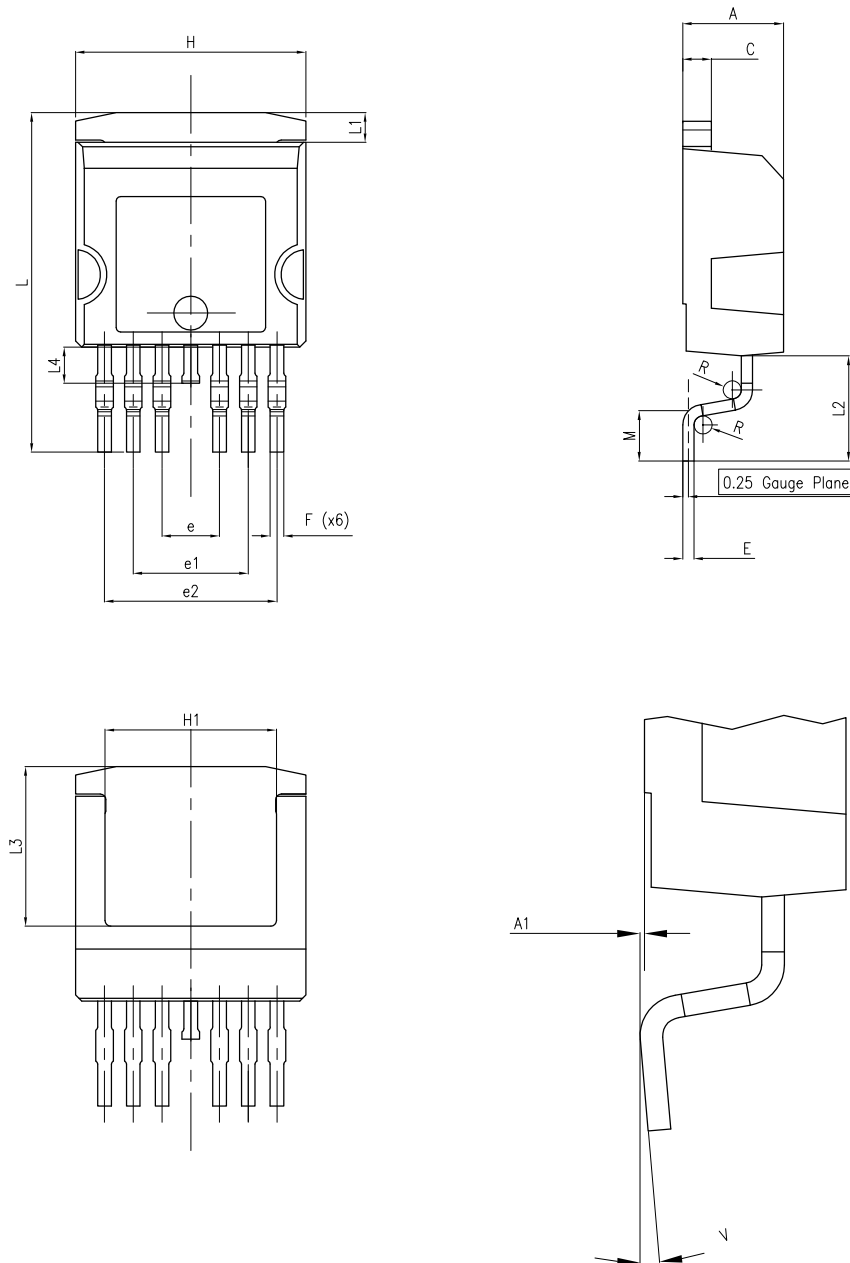
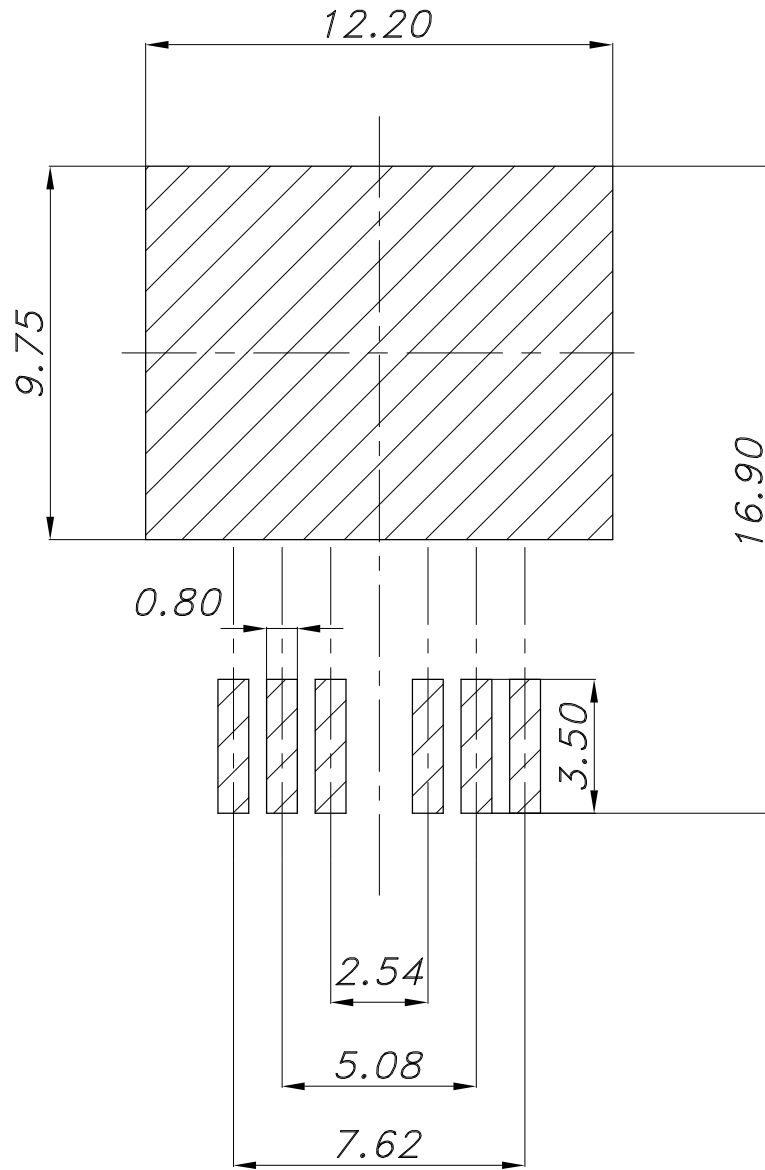


Table 8. H²PAK-6 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30		4.70
A1	0.03		0.20
C	1.17		1.37
e	2.34	2.54	2.74
e1	4.88		5.28
e2	7.42		7.82
E	0.45		0.60
F	0.50		0.70
H	10.00		10.40
H1	7.40		7.80
L	14.75		15.25
L1	1.27		1.40
L2	4.35		4.95
L3	6.85		7.25
L4	1.50		1.75
M	1.90		2.50
R	0.20		0.60
V	0°		8°

Figure 23. H²PAK-6 recommended footprint

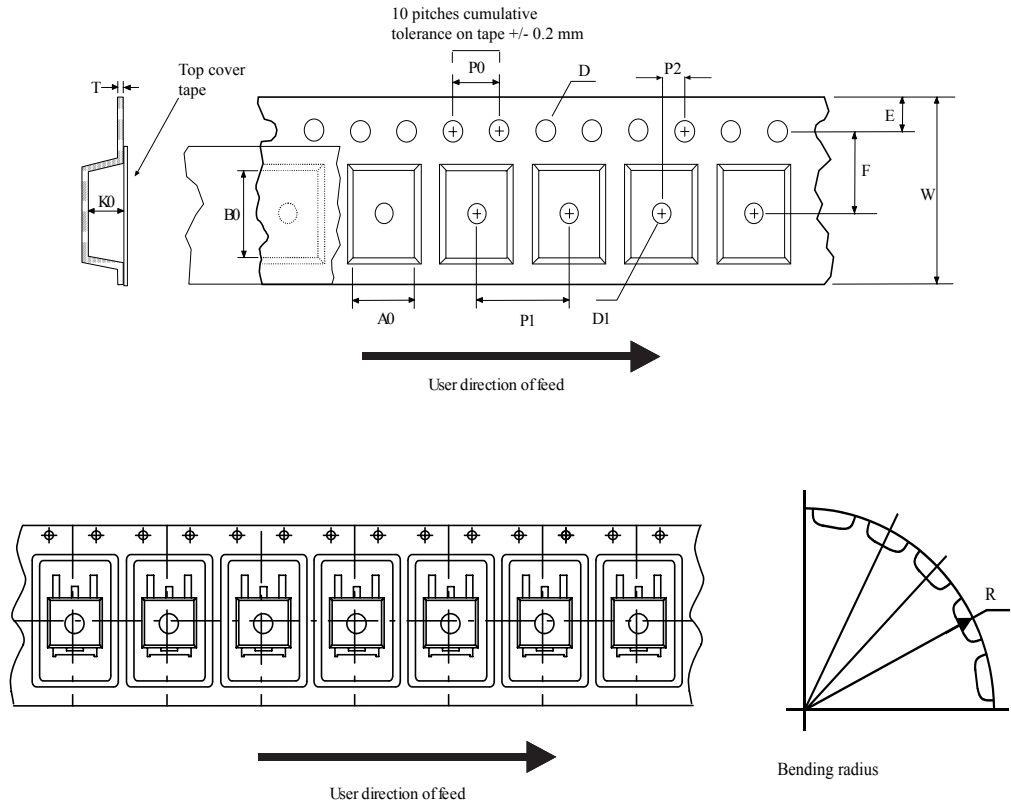


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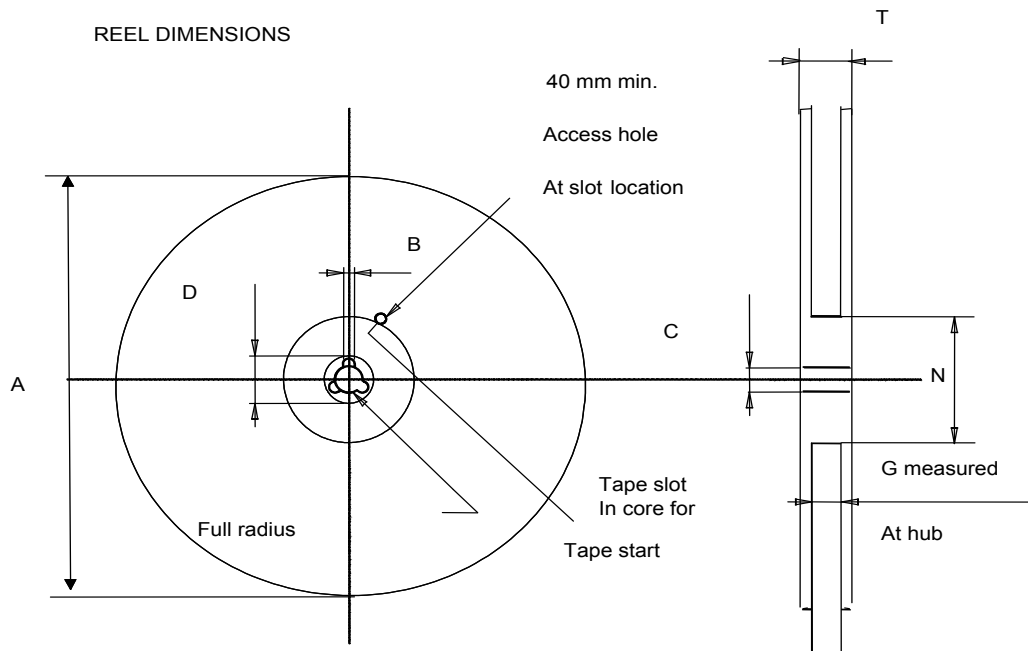
Note: Dimensions are in mm.

4.3 Packing information

Figure 24. Tape outline



AM08852v2

Figure 25. Reel outline

Table 9. Tape and reel mechanical data

Dim.	Tape		Dim.	Reel	
	mm			mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Revision history

Table 10. Document revision history

Date	Version	Changes
07-May-2014	1	Initial release.
23-Jul-2014	2	<ul style="list-style-type: none"> – Modified: title and description – Added: <i>Section 2.1: Electrical characteristics (curves)</i> – Minor text changes
06-Feb-2018	3	<ul style="list-style-type: none"> Removed maturity status indication from cover page. Production data. Modified Figure 3. Safe operating area. Minor text changes.

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

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